

In re: Hideki et al.  
Serial No.: 10/781,597  
Filed: February 18, 2004  
Page 3 of 12

**In the Claims:**

1. (Original) A phase-changeable memory device, comprising:  
a phase-changeable material pattern of a phase-changeable material that includes nitrogen atoms; and  
first and second electrodes electrically connected to the phase-changeable material pattern and provide an electrical signal thereto.
2. (Original) The device of Claim 1, wherein the phase-changeable material pattern has a polycrystalline structure.
3. (Original) The device of Claim 1, wherein an amount of the nitrogen atoms included in the phase-changeable material is from about 0.25% to about 25% with respect to the total atomic weight of ingredients of the phase-changeable material.
4. (Original) The device of Claim 1, wherein the phase-changeable material pattern comprises Ge-Sb-Te-N, As-Sb-Te-N, As-Ge-Sb-Te-N, Sn-Sb-Te-N, In-Sn-Sb-Te-N, Ag-In-Sb-Te-N, 5A group element-Sb-Te-N, 6A group element-Sb-Te-N, 5A group element-Sb-Se-N, and/or 6A group element-Sb-Se-N.
5. (Original) The device of Claim 1, wherein the first and second electrodes comprise a conductive material containing nitrogen, a conductive material containing carbon, titanium, tungsten, molybdenum, tantalum, titanium silicide, tantalum silicide and/or a combination thereof.
6. (Original) The device of Claim 5, wherein the first and/or second conductive electrodes further include one of aluminum (Al), aluminum-copper alloy (Al-Cu), aluminum-copper-silicon alloy (Al-Cu-Si), tungsten silicide (WSi), copper (Cu), tungsten titanium (TiW) and/or a combination thereof.
7. (Original) The device of Claim 5, wherein the conductive material containing nitrogen comprises titanium nitride (TiN), tantalum nitride (TaN), molybdenum nitride (MoN), niobium nitride (NbN), titanium silicon nitride (TiSiN), titanium aluminum

In re: Hideki et al.  
Serial No.: 10/781,597  
Filed: February 18, 2004  
Page 4 of 12

nitride (TiAlN), titanium boron nitride (TiBN), zirconium silicon nitride (ZrSiN), tungsten silicon nitride (WSiN), tungsten boron nitride (WBN), zirconium aluminum nitride (ZrAlN), molybdenum silicon nitride (MoSiN), molybdenum aluminum nitride (MoAlN), tantalum silicon nitride (TaSiN), tantalum aluminum nitride (TaAlN), titanium oxide nitride (TiON), titanium aluminum oxide nitride (TiAlON), tungsten oxide nitride (WON) and/or tantalum oxide nitride (TaON).

8. (Original) The device of Claim 1, further comprising:  
a transistor including a source region, a drain region and a gate electrode;  
a lower interconnection electrically connected to the drain region; and  
an upper metal interconnection electrically connected to one of the first and second electrodes;  
wherein the other of the first and second electrodes is electrically connected to the source region.

9. (Original) A phase-changeable memory device, comprising:  
a phase-changeable material pattern of a phase-changeable material having a polycrystalline structure; and  
first and second electrodes electrically connected to the phase-changeable material pattern to provide an electrical signal thereto.

10. (Original) The device of Claim 9, wherein the phase-changeable material pattern comprises Ge-Sb-Te-N, As-Sb-Te-N, As-Ge-Sb-Te-N, Sn-Sb-Te-N, In-Sn-Sb-Te-N, Ag-In-Sb-Te-N, a 5A group element-Sb-Te-N, a 6A group element-Sb-Te-N, a 5A group element-Sb-Se-N, and/or a 6A group element-Sb-Se-N.

11. (Original) The device of Claim 10, wherein an amount of nitrogen atoms in the phase-changeable material pattern is from about 0.25% to about 25% with respect to the total atomic weight of ingredients of the phase-changeable material.

12. (Original) A phase-changeable memory device, comprising:  
a transistor including a source region, a drain region and a gate electrode disposed

In re: Hideki et al.  
Serial No.: 10/781,597  
Filed: February 18, 2004  
Page 5 of 12

on the semiconductor substrate;

a lower interconnection electrically connected to the drain region;

a contact pad formed of the same material and placed on the same height as the lower interconnection;

a variable resistor electrically connected to the contact pad; and

an upper interconnection electrically connected to the variable resistor,

wherein the variable resistor is interposed between the two electrodes and includes nitrogen atoms.

13. (Original) The device of Claim 12, wherein the variable resistor includes a phase-changeable material pattern having a polycrystalline structure.

14. (Original) The device of Claim 13, wherein the variable resistor includes a phase-changeable material pattern that includes nitrogen atoms, wherein an amount of the nitrogen atoms is from about 0.25% to about 25% with respect to the total atomic weight of ingredients of the phase-changeable material.

15. (Original) The device of Claim 12, wherein the variable resistor includes a phase-changeable material pattern that includes nitrogen atoms, wherein an amount of the nitrogen atoms is from about 0.25% to about 25% with respect to the total atomic weight of ingredients of the phase-changeable material.

16. (Original) The device of Claim 12, wherein the phase-changeable material pattern comprises Ge-Sb-Te-N, As-Sb-Te-N, As-Ge-Sb-Te-N, Sn-Sb-Te-N, In-Sn-Sb-Te-N, Ag-In-Sb-Te-N, a 5A group element-Sb-Te-N, a 6A group element-Sb-Te-N, a 5A group element-Sb-Se-N, and/or a 6A group element-Sb-Se-N.

17. (Original) The device of Claim 12, wherein the first and second electrodes comprise a conductive material containing nitrogen, a conductive material containing carbon, titanium, tungsten, molybdenum, tantalum, titanium silicide, tantalum silicide and/or a combination thereof.

In re: Hideki et al.  
 Serial No.: 10/781,597  
 Filed: February 18, 2004  
 Page 6 of 12

18. (Original) The device of Claim 15, wherein the two electrodes comprise a conductive material containing nitrogen, a conductive material containing carbon, titanium, tungsten, molybdenum, tantalum, titanium silicide, tantalum silicide, and/or a combination thereof.

19. (Original) The device of claim 17, wherein one of the two electrodes is electrically connected to the contact pad and the other electrode is electrically connected to the upper interconnection,  
 wherein the other electrode connected to the top electrode further comprises aluminum (Al), aluminum-copper alloy (Al-Cu), aluminum-copper-silicon alloy (Al-Cu-Si), tungsten silicide (WSi), copper (Cu), tungsten titanium (TiW), and/or a combination thereof.

20. (Original) The device of claim 19, wherein the conductive material containing nitrogen comprises titanium nitride (TiN), tantalum nitride (Ta<sub>2</sub>N), molybdenum nitride (MoN), niobium nitride (NbN), titanium silicon nitride (TiSiN), titanium aluminum nitride (TiAlN), titanium boron nitride (TiBN), zirconium silicon nitride (ZrSiN), tungsten silicon nitride (WSiN), tungsten boron nitride (WBN), silicon aluminum nitride (ZrAlN), molybdenum silicon nitride (MoSiN), molybdenum aluminum nitride (MoAlN), tantalum silicon nitride (TaSiN), tantalum aluminum nitride (TaAlN), titanium oxide nitride (TiON), titanium aluminum oxide nitride (TiAlON), tungsten oxide nitride (WON) and/or tantalum oxide nitride (TaON).

21. (Original) A phase-changeable memory device comprising:  
 a transistor including a source region, a drain region and a gate electrode that are disposed on the semiconductor substrate;  
 an interlayer dielectric layer formed on the semiconductor substrate to cover the transistor;  
 a lower interconnection disposed in the interlayer dielectric layer to connect to the drain region electrically;  
 a contact pad disposed in the interlayer dielectric layer at substantially the same height and formed of the same material as the lower interconnection;

In re: Hideki et al.  
 Serial No.: 10/781,597  
 Filed: February 18, 2004  
 Page 7 of 12

a lower intermetal dielectric layer disposed on the interlayer dielectric layer;  
 a variable resistor electrically connected to the contact pad;  
 an upper intermetal dielectric layer disposed on the lower intermetal dielectric layer  
 to cover a side of the variable resistor; and  
 an upper interconnection disposed in the upper intermetal dielectric layer to connect  
 to the variable resistor electrically,  
 wherein the variable resistor comprises:  
 a bottom electrode penetrating a portion of the lower intermetal dielectric layer to  
 electrically connect to the contact pad;  
 a phase-changeable material pattern containing nitrogen atoms disposed on the  
 lower intermetal dielectric layer and on the bottom electrode ; and  
 a top electrode disposed on the phase-changeable material pattern to electrically  
 connect to the upper interconnection.

22. (Original) The device of Claim 21, wherein the phase-changeable material  
 pattern has a polycrystalline structure.

23. (Original) The device of claim 22, wherein an amount of the nitrogen atoms  
 is about from 0.25% to about 25% with respect to a total atomic weight of ingredients of the  
 phase-changeable material pattern.

24. (Original) The device of Claim 23, wherein the phase-changeable material  
 pattern comprises Ge-Sb-Te-N, As-Sb-Te-N, As-Ge-Sb-Te-N, Sn-Sb-Te-N, In-Sn-Sb-Te-N,  
 Ag-In-Sb-Te-N, a 5A group element-Sb-Te-N, a 6A group element-Sb-Te-N, a 5A group  
 element-Sb-Se-N, and/or a 6A group element-Sb-Se-N.

25. (Original) The device of Claim 24, wherein the bottom and top electrodes  
 comprise a conductive material containing nitrogen, a conductive material containing  
 carbon, titanium, tungsten, molybdenum, tantalum, titanium silicide, tantalum silicide,  
 and/or a combination thereof.

26. (Original) The device of Claim 25, wherein a top surface of the top electrode

In re: Hideki et al.  
 Serial No.: 10/781,597  
 Filed: February 18, 2004  
 Page 8 of 12

is lower than a top surface of the upper intermetal dielectric layer, and  
 further comprising a conductive plug penetrating the intermetal dielectric layer on  
 the top electrode to electrically connect to the upper interconnection,  
 wherein a diameter of the conductive plug is smaller than a width of the top  
 electrode and the conductive plug comprises aluminum (Al), aluminum-copper alloy (Al-  
 Cu), aluminum-copper-silicon alloy (Al-Cu-Si), tungsten silicide (WSi), copper (Cu),  
 tungsten titanium (TiW), and/or a combination thereof.

27. (Original) The device of Claim 26, wherein the conductive material  
 containing nitrogen comprises titanium nitride (TiN), tantalum nitride (TaN), molybdenum  
 nitride (MoN), niobium nitride (NbN), titanium silicon nitride (TiSiN), titanium aluminum  
 nitride (TiAlN), titanium boron nitride (TiBN), zirconium silicon nitride (ZrSiN), tungsten  
 silicon nitride (WSiN), tungsten boron nitride (WBN), silicon aluminum nitride (ZrAlN),  
 molybdenum silicon nitride (MoSiN), molybdenum aluminum nitride (MoAlN), tantalum  
 silicon nitride (TaSiN), tantalum aluminum nitride (TaAlN), titanium oxide nitride (TiON),  
 titanium aluminum oxide nitride (TiAlON), tungsten oxide nitride (WON) and/or tantalum  
 oxide nitride (TaON).

28.-50. (Canceled)

51. (New) The device of Claim 1 wherein the polycrystalline structure includes  
 grains of less than about 100 nm in size.

52. (New) The device of Claim 9 wherein the polycrystalline structure includes  
 grains of less than about 100 nm in size.